

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI AVD002P** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	250 mA
<b>V<sub>CC</sub></b>	37 V
<b>P<sub>DISS</sub></b>	10 W @ T <sub>C</sub> ≤ 100 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	10 °C/W

**PACKAGE STYLE .280 4L PILL (A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

**ORDER CODE: ASI10553**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 1 mA	45			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 5 mA      R <sub>BE</sub> = 10 Ω	45			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1 mA	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 35 V			1.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 100 A	30		300	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 35 V      P <sub>OUT</sub> = 2.0 W      f = 1025 – 1150	9.0			<b>dB</b>
<b>η<sub>c</sub></b>	MHZ	35			<b>%</b>